

## Abstract of the Disclosure

Disclosed is a method for forming bit lines of a semiconductor device capable of solving an issue on overlay between a bit line contact and a bit line when bit lines of DRAM are formed. The method comprises the steps of preparing a semiconductor substrate where active areas and device isolation areas are defined, forming a device isolation layer on the device isolation areas, forming a plurality of word lines on the substrate at a constant interval; forming source/drain dopant areas on the active areas on both sides of each word line, forming landing plugs contacting with the source/drain dopant areas in a matrix form, forming first, second and third insulation layers in sequence on a front surface of the substrate including the word lines, defining areas for bit lines through alternative etching of the second and second insulation layers, forming bit line contact holes through alternative etching of the first insulation layer so as to alternatively expose the landing plugs, and forming bit lines within the bit line areas including the bit line contact holes.